Product data sheet

1. General description

Silicon Carbide Schottky diode in a SOD59A(TO-220AC) plastic package, designed for high frequency switched-mode power supplies

2. Features and benefits

- · Highly stable switching performance
- · High forward surge capability IFSM
- Extremely fast reverse recovery time
- Superior in efficiency to Silicon Diode alternatives
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant

3. Applications

- Power factor correction
- Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- Motor Drives

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{RRM}	repetitive peak reverse voltage			-	-	650	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _{mb} \leq 110 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3; Fig. 4		-	-	12	Α
Static characte	Static characteristics						
V _F	forward voltage	I _F = 12 A; T _j = 25 °C; <u>Fig. 6</u>		-	1.5	1.7	V
		I _F = 12 A; T _j = 150 °C; <u>Fig. 6</u>		-	1.8	2.1	V

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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	K — A 001aaa020
2	Α	anode	$rac{1}{2} \bigcirc \zeta$	001aaa020
mb	mb	mounting base; connected to cathode	TO-220AC (SOD59A)	

6. Ordering information

Table 3. Ordering information

Type number	Package	ckage						
	Name	Description	Version					
NXPSC12650	TO-220AC	Plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59A					

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7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	650	V
V_{RWM}	crest working reverse voltage		-	650	V
V_R	reverse voltage	DC	-	650	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _{mb} ≤ 110 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3; Fig. 4	-	12	Α
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 μ s; square-wave pulse	-	24	Α
I _{FSM}	non-repetitive peak	t_p = 10 ms; $T_{j(init)}$ = 25 °C; SIN	-	72	Α
	forward current	t _p = 10 μs; Τ _{j(init)} = 25 °C; SIN	-	620	А
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-	175	°C

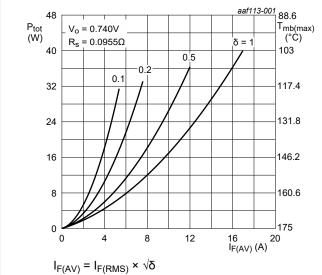


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

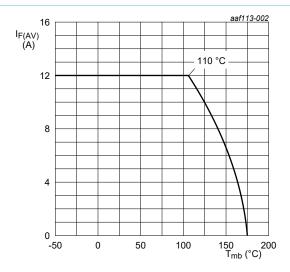


Fig. 2. Forward current as a function of mounting base temperature; maximum values

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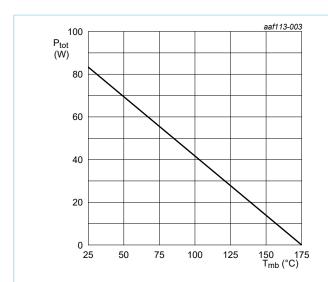


Fig. 3. Total power dissipation as a function of mounting base temperature

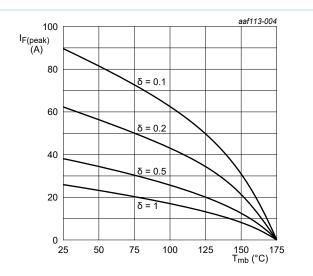


Fig. 4. Current derating as a function of mounting base temperature

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8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	-	1.8	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W

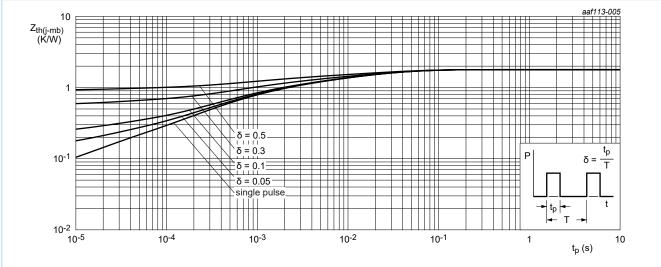


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

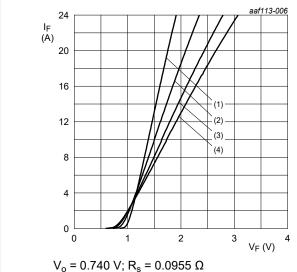
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9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static chara	Static characteristics						
V _F	forward voltage	I _F = 12 A; T _j = 25 °C; <u>Fig. 6</u>		-	1.5	1.7	V
		I _F = 12 A; T _j = 150 °C; <u>Fig. 6</u>		-	1.8	2.1	V
I _R	reverse current	V _R = 650 V; T _j = 25 °C		_	-	80	μA
		V _R = 650 V; T _j = 150 °C		_	-	320	μA
Dynamic cha	Dynamic characteristics				,		
Q _r	recovered charge	$I_F = 12 \text{ A; } dI_F/dt = 500 \text{ A/}\mu\text{s;}$ $V_R = 400 \text{ V; } T_j = 25 \text{ °C; } Fig. 7$		-	18	-	nC
C _d	diode capacitance	f = 1 MHz; V _R = 1 V; T _j = 25 °C		-	380	-	pF
		f = 1 MHz; V _R = 300 V; T _j = 25 °C		-	60	-	pF
		f = 1 MHz; V _R = 600 V; T _j = 25 °C		-	58	-	pF



(1) $T_j = 25$ °C; typical values (2) $T_j = 100$ °C; typical values (3) $T_j = 150$ °C; typical values (4) $T_j = 175$ °C; typical values

Fig. 6. Forward current as a function of forward voltage; typical values

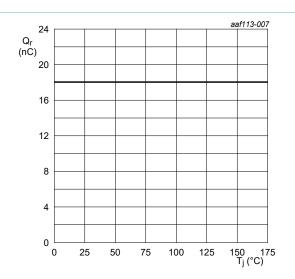
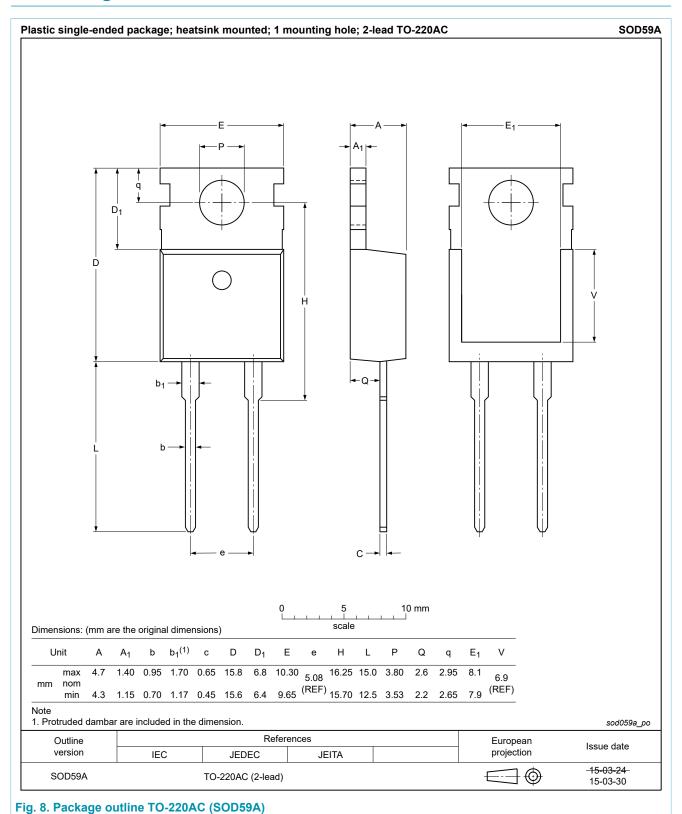


Fig. 7. Recovered charge as a function of junction temperature

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10. Package outline



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11. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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